# MGSF1N02LT1

**Preferred Device** 

# Power MOSFET 750 mAmps, 20 Volts

# N-Channel SOT-23

These miniature surface mount MOSFETs low  $R_{DS(on)}$  assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are dc–dc converters and power management in portable and battery–powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

### Features

- Low R<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- Pb–Free Packages are Available

**MAXIMUM RATINGS** (T<sub>J</sub> =  $25^{\circ}$ C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	20	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	± 20	Vdc
Drain Current – Continuous @ $T_A = 25^{\circ}C$ – Pulsed Drain Current ( $t_p \le 10 \ \mu s$ )	I <sub>D</sub> I <sub>DM</sub>	750 2000	mA
Total Power Dissipation @ $T_A = 25^{\circ}C$	PD	400	mW
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	300	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	ΤL	260	°C

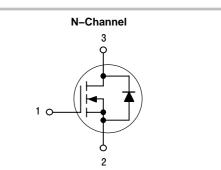
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



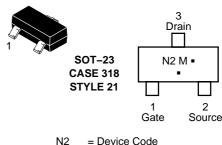
## **ON Semiconductor®**

http://onsemi.com

# 750 mAMPS, 20 VOLTS R<sub>DS(on)</sub> = 90 m $\Omega$



MARKING DIAGRAM/ PIN ASSIGNMENT



M = Date Code\*

= Pb–Free Package

(Note: Microdot may be in either location) \*Date Code orientation and overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MGSF1N02LT1	SOT-23	3000/Tape & Reel
MGSF1N02LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
MGSF1N02LT3	SOT-23	10,000/Tape & Reel
MGSF1N02LT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

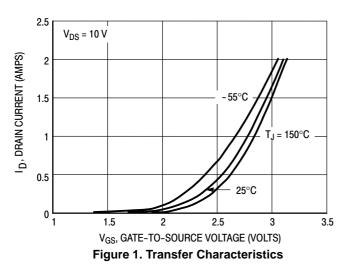
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

 $\ensuremath{\textbf{Preferred}}$  devices are recommended choices for future use and best overall value.

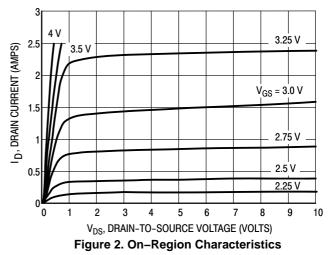
## MGSF1N02LT1

Chara	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS		•				
Drain-to-Source Breakdown Voltag $(V_{GS} = 0 \text{ Vdc}, I_D = 10 \mu \text{Adc})$	V <sub>(BR)DSS</sub>	20	-	_	Vdc	
Zero Gate Voltage Drain Current ( $V_{DS} = 20$ Vdc, $V_{GS} = 0$ Vdc) ( $V_{DS} = 20$ Vdc, $V_{GS} = 0$ Vdc, $T_J =$	I <sub>DSS</sub>			1.0 10	μAdc	
Gate-Body Leakage Current (V <sub>GS</sub> =	I <sub>GSS</sub>	-	-	±100	nAdc	
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 250 \mu Adc$ )	V <sub>GS(th)</sub>	1.0	1.7	2.4	Vdc	
$      Static Drain-to-Source On-Resistation \\       (V_{GS} = 10 \ Vdc, \ I_D = 1.2 \ Adc) \\       (V_{GS} = 4.5 \ Vdc, \ I_D = 1.0 \ Adc) $	r <sub>DS(on)</sub>		0.075 0.115	0.090 0.130	Ω	
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V <sub>DS</sub> = 5.0 Vdc)	C <sub>iss</sub>	-	125	-	pF
Output Capacitance	(V <sub>DS</sub> = 5.0 Vdc)	C <sub>oss</sub>	-	120	-	
Transfer Capacitance	(V <sub>DG</sub> = 5.0 Vdc)	C <sub>rss</sub>	-	45	-	1
SWITCHING CHARACTERISTICS (I	Note 2)					
Turn-On Delay Time		t <sub>d(on)</sub>	-	2.5	-	ns
Rise Time	(V <sub>DD</sub> = 15 Vdc, I <sub>D</sub> = 1.0 Adc,	t <sub>r</sub>	-	1.0	-	
Turn-Off Delay Time	R <sub>L</sub> = 50 Ω)	t <sub>d(off)</sub>	-	16	-	
Fall Time		t <sub>f</sub>	-	8.0	-	
Gate Charge (See Figure 6)		QT	_	6000	-	pC
SOURCE-DRAIN DIODE CHARACT	FERISTICS					
Continuous Current	I <sub>S</sub>	_	-	0.6	А	
Pulsed Current	I <sub>SM</sub>	_	-	0.75	-	
Forward Voltage (Note 2)	V <sub>SD</sub>	-	0.8	-	V	

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
Switching characteristics are independent of operating junction temperature.

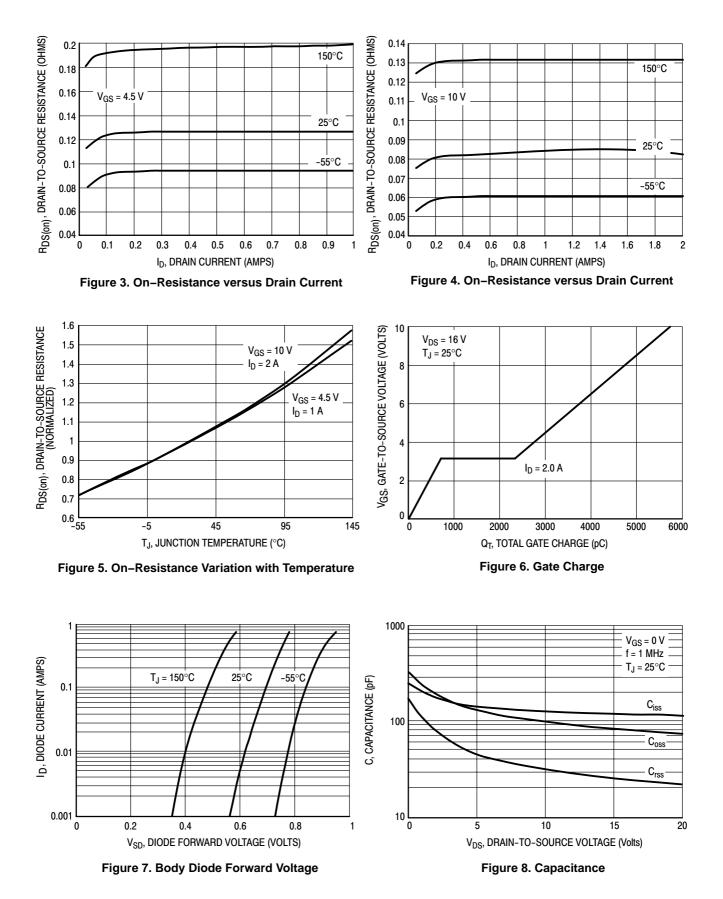


### **TYPICAL ELECTRICAL CHARACTERISTICS**



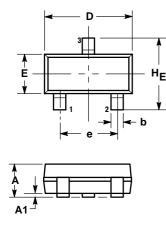
## MGSF1N02LT1

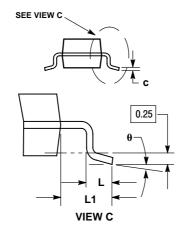
## **TYPICAL ELECTRICAL CHARACTERISTICS**



#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN** 





NOTES: I. DIMENSIONING AND TOLERANCING PEF ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: INCH.
MAXIMUM LEAD THICKNESS INCLUDES
TOLEVISION TRUCKNESS INCLUDES DIMENSIONING AND TOLERANCING PER

LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF

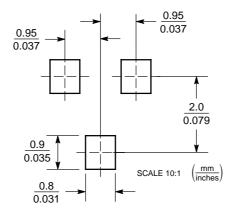
BASE MATERIAL.

318–01 THRU –07 AND –09 OBSOLETE, NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
с	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 21: PIN 1. GATE 2. SOURCE 3 DRAIN

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC products are not designed, intended, or authorized for use a components in systems intended for surgical implant into the body, or other applications and actual performance may any content applications. intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, ad distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, and claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative